# **BUK7K35-60E**

# Dual N-channel 60 V, 30 mΩ standard level MOSFET 15 November 2013 Product

**Product data sheet** 

# 1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> of greater than 1 V at 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	20.7	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	38	W
Static characte	Static characteristics FET1 and FET2						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	24	30	mΩ
Dynamic characteristics FET1 and FET2							
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 14; Fig. 13$		-	4.7	-	nC



Dual N-channel 60 V, 30 m $\Omega$  standard level MOSFET

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	1	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	_	mbk725
7	D1	drain1	1 2 3 4 <b>LFPAK56D (SOT1205)</b>	
8	D1	drain1	21.7.1.1005 (0011200)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7K35-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K35-60E	73560E

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$	-	60	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC	-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	20.7	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	17	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4	-	95	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	38	W
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Product data sheet

15 November 2013

2 / 13

#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode FET1 and FET2						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	20.7	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	95	Α
Avalanche Ruggedness FET1 and FET2						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 20.7 \text{ A}; V_{sup} \le 60 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; Fig. 3$	[1][2]	-	20.3	mJ

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

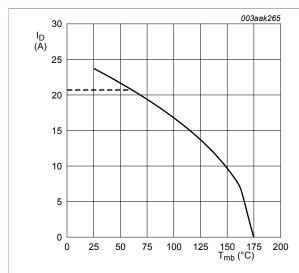


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$ 

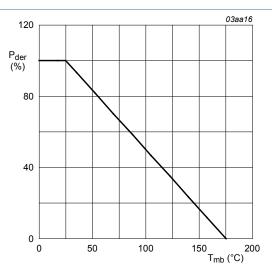


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times 100 \%$$

#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET

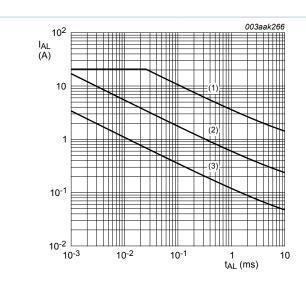
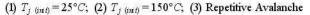


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



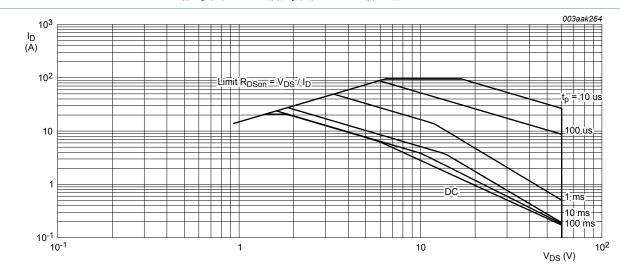


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

### 9. Thermal characteristics

Table 6. Thermal characteristics

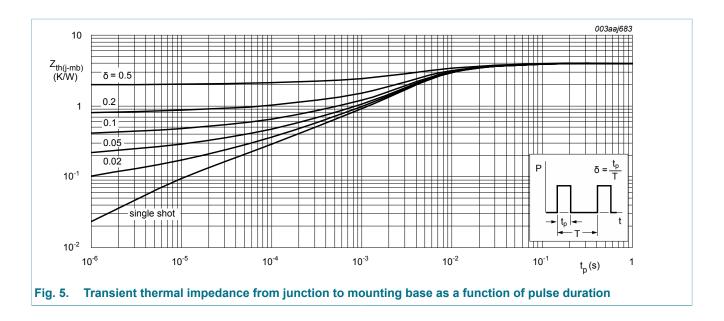
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	3.96	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET



## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 9; Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9; Fig. 10	-	-	4.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$	-	24	30	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	54	67	mΩ
Dynamic ch	naracteristics FET1 and FE	ET2				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	12.5	-	nC
$Q_{GS}$	gate-source charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V;	-	2.8	-	nC
$Q_{GD}$	gate-drain charge	e-drain charge $T_j = 25 \text{ °C}; Fig. 14; Fig. 13$	-	4.7	-	nC

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#### Dual N-channel 60 V, 30 mΩ standard level MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 48 V; T <sub>j</sub> = 25 °C; Fig. 14; Fig. 13	-	4.9	-	V
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	596	794	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	97	117	pF
C <sub>rss</sub>	reverse transfer capacitance		-	67	92	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 48 \text{ V}; R_L = 10 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_j = 25 \text{ °C}; I_D = 5 \text{ A}$	-	5.2	-	ns
t <sub>r</sub>	rise time		-	7	-	ns
t <sub>d(off)</sub>	turn-off delay time	_	-	10	-	ns
t <sub>f</sub>	fall time		-	7.2	-	ns
Source-dra	ain diode FET1 and FET2					
V <sub>SD</sub>	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	18.5	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	15.2	-	nC

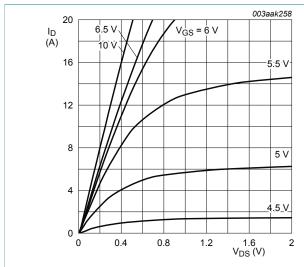


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



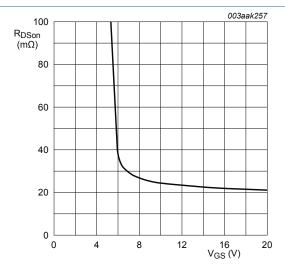


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C;  $I_D = 5A$ 

#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET

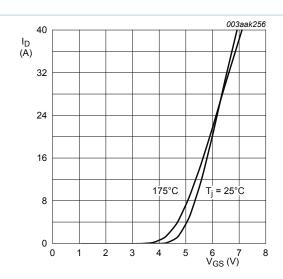


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

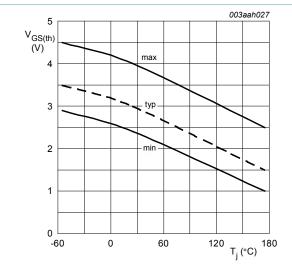


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

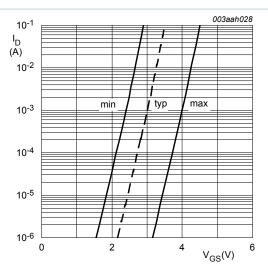


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

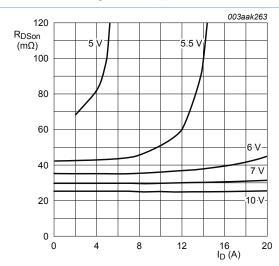


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25$$
°C

#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET

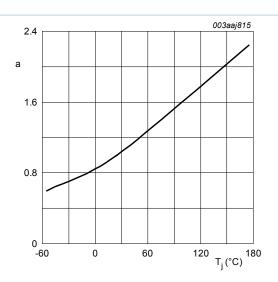


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

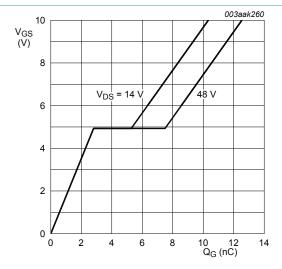


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C;  $I_D = 5A$ 

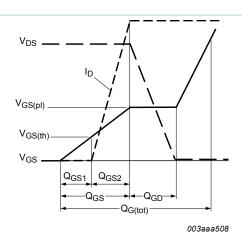


Fig. 13. Gate charge waveform definitions

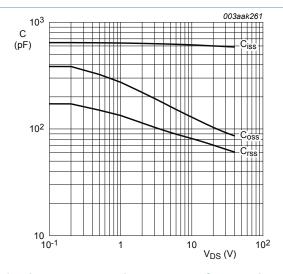


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET

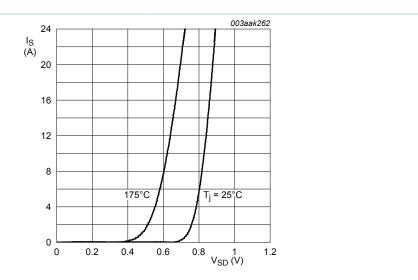
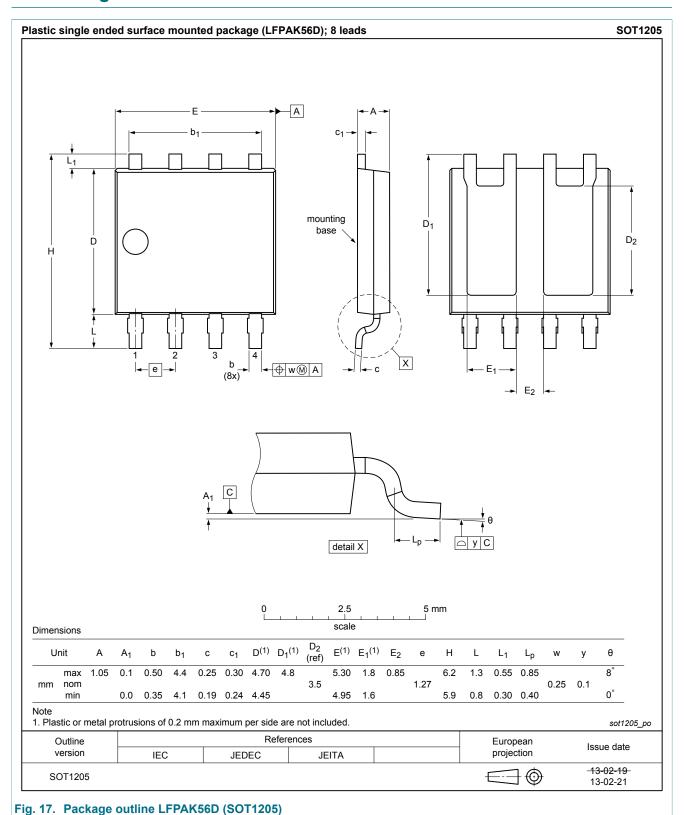


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET

# 11. Package outline



#### Dual N-channel 60 V, 30 mΩ standard level MOSFET

### 12. Legal information

#### 12.1 Data sheet status

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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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#### Dual N-channel 60 V, 30 m $\Omega$ standard level MOSFET

## 13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	
7	Marking	2
8	Limiting values	
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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13 / 13

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